

IN THE CLAIMS:

1. (Currently Amended) A laser CVD device comprising:
a plasma unit for turning pretreating gas into a plasma state in [atmosphere] air and
supplying a plasma gas to a substrate;
means for radiating a laser beam to a deposition area on the substrate;
means for supplying film forming gas to the deposition area; and
means for sealing the film forming gas isolated from an external atmosphere, wherein
the deposition area of said substrate is pretreated by said plasma unit supplying the
plasma gas to the substrate prior to a film formed by CVD over said deposition area of said
substrate by activating the film forming gas by said laser beam.

2. (Previously Presented) The laser CVD device as claimed in claim 1, wherein said
plasma unit makes the plasma state by arc discharge.

3. (Previously Presented) The laser CVD device as claimed in claim 1, further
comprising a X-Y table on which said substrate is posited.

4. (Previously Presented) The laser CVD device as claimed in claim 2, wherein said
plasma unit includes a plasma generating chamber, a gas inlet for receiving pretreating gas to
the plasma generating chamber, and an electrode for causing the pretreating gas to generate arc
discharge.

5. (Previously Presented) The laser CVD device as claimed in claim 4, wherein said plasma unit further includes a metal net for preventing the arc discharge from being effected on the substrate.

6. (Previously Presented) The laser CVD device as claimed in claim 1, wherein said pretreating gas is one of air, nitrogen and argon.

7. (Withdrawn) A laser CVD method comprising steps of:
turning pretreating gas into a plasma state by arc discharge;
supplying said pretreating gas in the plasma state to bring it into contact with a film formation face of a substrate;
supplying film forming gas to the film formation face of the substrate isolated from the external atmosphere;
irradiating the film formation face of said substrate with a laser beam to activate said film forming gas; and
causing said activated film forming gas to form a film over said film formation face of the substrate.

8. (Previously Presented) A pattern defect correcting apparatus comprising:
a substrate holder capable of moving a substrate having a pattern, said pattern having a defective portion;
a pretreating unit for turning pretreating gas into a plasma state by arc discharge in air and for supplying plasma state gas to the substrate on said substrate holder;

a film forming unit which is provided with means for radiating a laser beam and means for sealing film forming gas isolated from an external atmosphere; and

a control unit, wherein

said control unit controls said pretreating unit to supply as pretreatment prior to the CVD of the film the plasma state gas to the defective portion on said substrate,

said control unit controls said film forming unit to isolate said film forming gas from an external atmosphere and to supply said film forming gas onto the defective portion on said substrate, and

said control unit controls said film forming unit to irradiate the defective portion on said substrate with said laser beam to activate said film forming for the CVD, thereby causing film formation at the defective portion on said substrate.

9. (Canceled)

10. (New) A laser CVD device comprising:

a plasma unit for turning pretreating gas into a plasma state in atmosphere via arc discharge and supplying a plasma gas to a substrate, wherein said plasma unit includes a plasma generating chamber, a gas inlet for receiving pretreating gas to the plasma generating chamber, and an electrode for causing the pretreating gas to generate arc discharge, and a metal net for preventing the arc discharge from being effected on the substrate.;

means for radiating a laser beam to a deposition area on the substrate;

means for supplying film forming gas to the deposition area; and

means for sealing the film forming gas isolated from an external atmosphere, wherein

the deposition area of said substrate is pretreated by said plasma unit supplying the plasma gas to the substrate prior to a film formed by CVD over said deposition area of said substrate by activating the film forming gas by said laser beam.